

# P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
- 20	6.6 at V <sub>GS</sub> = - 4.5 V	- 42	63 nC			
	8.9 at V <sub>GS</sub> = - 2.5 V	- 42				

#### **FEATURES**

- DT-Trench Power MOSFET
- Low R<sub>DS(ON)</sub>×FOM
- Extremely low switching loss

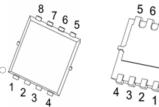


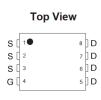
### **APPLICATIONS**

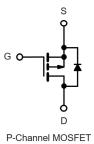
- Load switch
- Battery protection

PDFN3.3\*3.3-8L Pin Configuration

Top View Bottom View







<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	- 20	V			
Gate-Source Voltage	V <sub>GS</sub>	± 12				
Continuous Drain Current /T 150 °C)2	T <sub>C</sub> = 25 °C	1	- 42	А		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	⊢ I <sub>D</sub>	- 30			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 168				
Single Avalanche Energy	E <sub>AS</sub>	305	mJ			
Maximum Dawar Dissinations	T <sub>C</sub> = 25 °C	В	78	W		
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	$ P_D$	31.2			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	62 °C/W			
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.6	7 6/**		

#### Notes

- $a. \ \ Calculated \ continuous \ current \ based \ on \ maximum \ allowable junction \ temperature.$
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	0 μΑ - 20 -		-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.4	-	- 1	<b>,</b>	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	- 1	μA	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 8 A	-	6.6	7.9	mΩ	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -8 \text{ A}$	-	8.9	11		
		$V_{GS} = -1.8 \text{ V}, I_D = -8 \text{ A}$	-	13.2	17	]	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 10 A		70		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	4550	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 10 V, f = 100 MHz	-	586	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	543	-		
Total Gate Charge <sup>c</sup>	Qg		-	63	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -8 \text{ A}$	-	10	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	15	-		
Gate Resistance	$R_g$	f = 1 MHz	-	4.5	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	18	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -8 \text{ A},$	-	52	-	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$V_{GS}$ = - 4.5 V, $R_{g}$ = 0.5 Ω	-	95	-		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	40	-		
Drain-Source Body Diode Ratings ar	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	- 42	Α	
Pulsed Current	I <sub>SM</sub>		-	-	- 168	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -8 A, V <sub>GS</sub> = 0 V	-	-	- 1.2	V	
Reverse Recovery Time	t <sub>rr</sub>		-	60	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> = - 8 A, di/dt = 100 A/µs	-	55	-	nC	

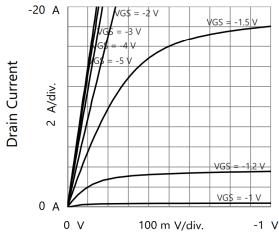
#### **Notes**

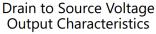
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

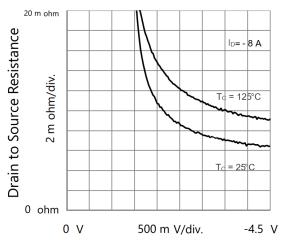
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



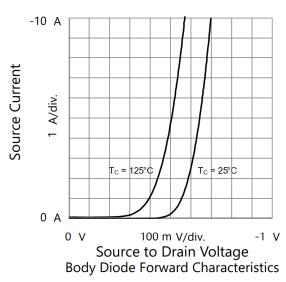
### TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

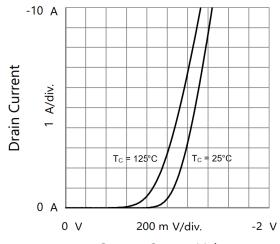




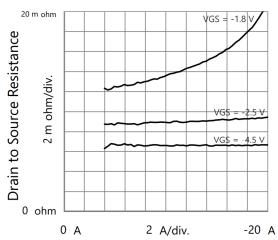


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

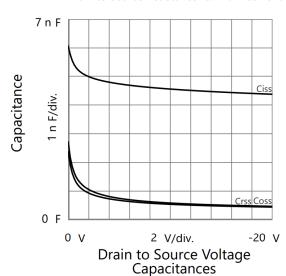




Gate to Source Voltage Transfer Characteristics

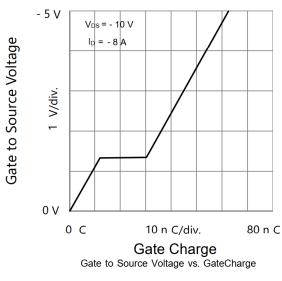


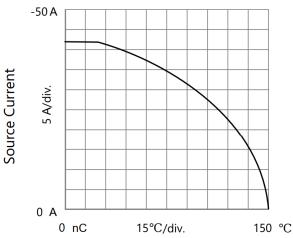
Drain Current
Drain to Source Resistance vs. Drain Current



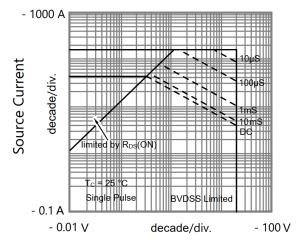


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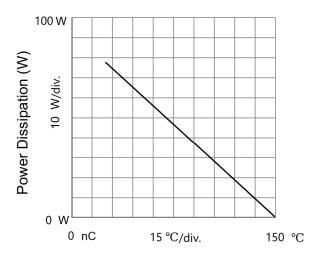




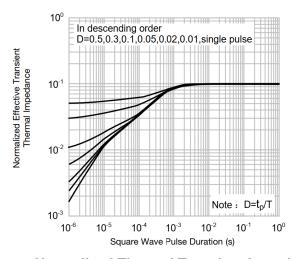
T<sub>C</sub> - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



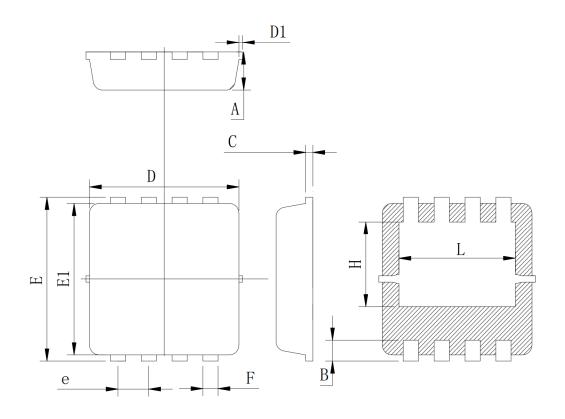
T<sub>C</sub> - Case Temperature



**Normalized Thermal Transient Impedance** 



### **PDFN 3.3X3.3 PACKAGE OUTLINE**



**COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	0.600	0.775	1.000
В	0.20	0.38	0.55
С	0.05	0.15	0.40
D	2.80	3.15	3.60
D1	-	-	0.15
Е	3.00	3.35	3.70
E1	2.60	3.10	3.45
e	0.50	0.65	0.80
F	0.15	0.32	0.45
Н	1.25	1.73	2.10
L	2.20	2.45	2.85





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